Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently amended) A light emitting diode, comprising:

a semiconductor substrate;

a light-emitting region including an active layer provided between a first conductivity type cladding layer formed over [[on]] the semiconductor substrate and a second conductivity type cladding layer;

a transparent conductive film made of a metal oxide and located over the light-emitting region;

a first electrode formed on the upper side of the transparent conductive film;

a second electrode formed on the whole or a part of the bottom of the semiconductor substrate;

a layer for preventing exfoliation of the transparent conductive film, the preventing layer being made of a compound semiconductor containing at least aluminum and located between the light-emitting region and the transparent conductive film, the preventing layer having a high carrier concentration; and

an undoped layer or a low carrier concentration layer formed between the active layer and the second conductivity type cladding layer, wherein the undoped layer or the low carrier concentration layer is a layer other than the active layer and comprises a bandgap greater than the active layer.

2. (Original) The light emitting diode as defined in claim 1, wherein:

the preventing layer contains a conductivity type determination impurity at a concentration of 1×10^{19} cm^{-3} or higher.

3. (Original) The light emitting diode as defined in claim 1, wherein:

the preventing layer has a film thickness of 300 nm or less.

4. (Original) The light emitting diode as defined in claim 2, wherein:

the preventing layer has a film thickness of 300 nm or less.

5. (Original) The light emitting diode as defined in claim 1, wherein:
the transparent conductive film is made of indium tin oxide.

6. (Original) The light emitting diode as defined in claim 2, wherein:
the transparent conductive film is made of indium tin oxide.

7. (Original) The light emitting diode as defined in claim 1, wherein:
the preventing layer is made of an arsenic compound.

8. (Original) The light emitting diode as defined in claim 2, wherein:
the preventing layer is made of an arsenic compound.

9. (Original) The light emitting diode as defined in claim 1, wherein:
the light-emitting region is made of $(Al_XGa_{1-X})_YIn_{1-Y}P$ ($0 \leq X \leq 1$, $0 \leq Y \leq 1$).

10. (Original) The light emitting diode as defined in claim 2, wherein:
the light-emitting region is made of $(Al_XGa_{1-X})_YIn_{1-Y}P$ ($0 \leq X \leq 1$, $0 \leq Y \leq 1$).

11. (Original) The light emitting diode as defined in claim 1, wherein:
the preventing layer is an AlGaAs layer having a bandgap which is smaller than that of the active layer; and
the AlGaAs layer is made of $Al_XGa_{1-X}As$ ($0.01 \leq X \leq 0.43$).

12. (Previously presented) The light emitting diode as defined in claim 1, wherein:
the preventing layer has a carrier concentration of 1×10^{19} cm^{-3} or higher.

13. (Original) The light emitting diode as defined in claim 11, wherein:
the AlGaAs layer has a carrier concentration of 1×10^{19} cm^{-3} or higher.

14. (Previously presented) The light emitting diode as defined in claim 1, wherein:
the preventing layer is added with at least one of Zn, Be, and Mg.

15. (Original) The light emitting diode as defined in claim 11, wherein:
the AlGaAs layer is added with at least one of Zn, Be, and Mg.

16. (Previously presented) The light emitting diode as defined in claim 1, wherein:
the preventing layer is added with at least one of Zn, Be and Mg, and C; and
C is autodoped.

17. (Original) The light emitting diode as defined in claim 11, wherein:
the AlGaAs layer is added with at least one of Zn, Be and Mg, and C; and
C is autodoped.

18. (Previously presented) The light emitting diode as defined in claim 1, wherein:
the preventing layer is formed at a growth temperature of 600°C or lower.

19. (Original) The light emitting diode as defined in claim 11, wherein:
the AlGaAs layer is formed at a growth temperature of 600°C or lower.

20. (Previously presented) The light emitting diode as defined in claim 1, wherein:
the preventing layer is formed at a V/III ratio in raw materials of 50 or less at the time of growth.

21. (Original) The light emitting diode as defined in claim 11, wherein:
the AlGaAs layer is formed at a V/III ratio in raw materials of 50 or less at the time of growth.

22. (Original) The light emitting diode as defined in claim 11, wherein:
the transparent conductive film is made of indium tin oxide.

23. (Original) The light emitting diode as defined in claim 11, wherein:
the light-emitting region is made of $(Al_XGa_{1-X})_YIn_{1-Y}P$ ($0 \leq X \leq 1$, $0 \leq Y \leq 1$).